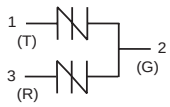
Compak Two-chip *SIDACtor* Device



The modified DO-214AA *SIDACtor* device provides low-cost, longitudinal protection.

SIDACtor devices are used to enable equipment to meet various regulatory requirements including GR 1089, ITU K.20, K.21, and K.45, IEC 60950, UL 60950, and TIA-968 (formerly known as FCC Part 68).

Electrical Parameters

Part Number	V_{DRM} Volts	V_S Volts	V_{DRM} Volts	V_S Volts	V_T Volts	I_{DRM} µAmps	I_S mAmps	I_T Amps	I_H mAmps	C_O pF
	Pins1-2, 2-3		Pins 1-3							Pins 1-3
P1402C_	58	77	116	154	4	5	800	2.2	120	15
P1602C_	65	95	130	190	4	5	800	2.2	120	15
P2202C_	90	130	180	260	4	5	800	2.2	120	15
P2702C_	120	160	240	320	4	5	800	2.2	120	15
P3002C_	140	180	280	360	4	5	800	2.2	120	15
P3602C_	170	220	340	440	4	5	800	2.2	120	15
P4202C_	190	250	380	500	4	5	800	2.2	120	15
P4802C_	220	300	440	600	4	5	800	2.2	120	15
P6002C_	275	350	550	700	4	5	800	2.2	120	15

* For surge ratings, see table below.

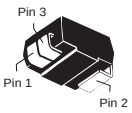
General Notes:
- All measurements are made at an ambient temperature of 25 °C. I_{PP} applies to -40 °C through +85 °C temperature range.
- I_{PP} is a repetitive surge rating and is guaranteed for the life of the product.
- Listed *SIDACtor* devices are bi-directional. All electrical parameters and surge ratings apply to forward and reverse polarities.
- V_{DRM} is measured at I_{DRM}.
- V_S is measured at 100 V/µs.
- Special voltage (V_S and V_{DRM}) and holding current (I_H) requirements are available upon request.
- Off-state capacitance (C_O) is measured between Pins 1-3 at 1 MHz with a 2 V bias.
- UL 60950 creepage requirements must be considered.

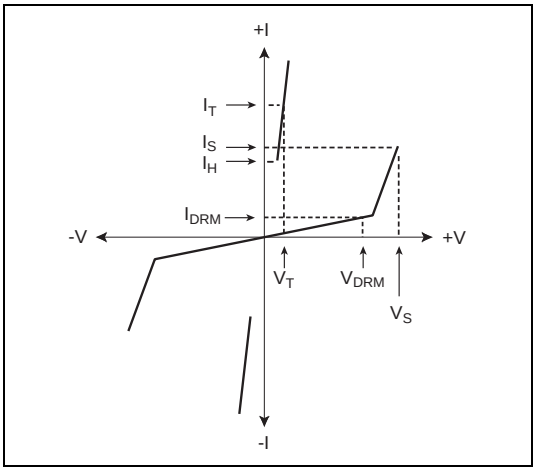
Surge Ratings

Series	I_{PP} 2x10 µs Amps	I_{PP} 8x20 µs Amps	I_{PP} 10x160 µs Amps	I_{PP} 10x560 µs Amps	I_{PP} 10x1000 µs Amps	I_{TSM} 60 Hz Amps	di/dt Amps/µs
A	150	150	90	50	45	20	500
B *	250	250	150	100	80	30	500

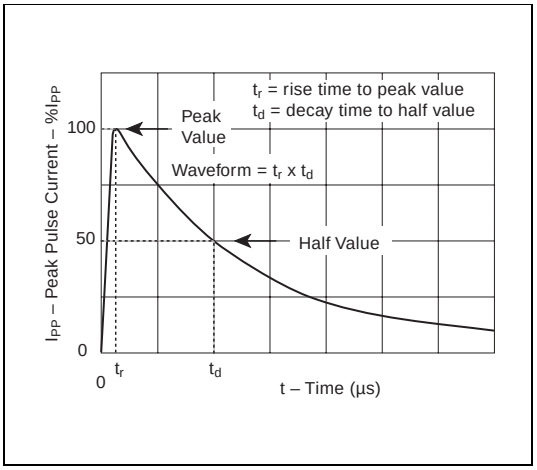
* Contact factory for release date.

Thermal Considerations

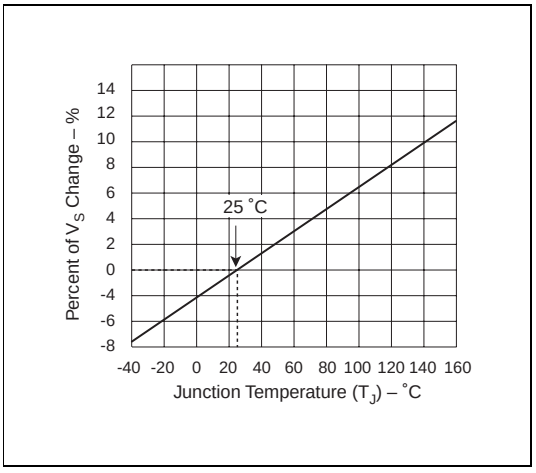
Package	Symbol	Parameter	Value	Unit
Modified DO-214AA 	T_J	Operating Junction Temperature Range	-40 to +150	°C
	T_S	Storage Temperature Range	-65 to +150	°C
	$R_{\theta JA}$	Thermal Resistance: Junction to Ambient	85	°C/W



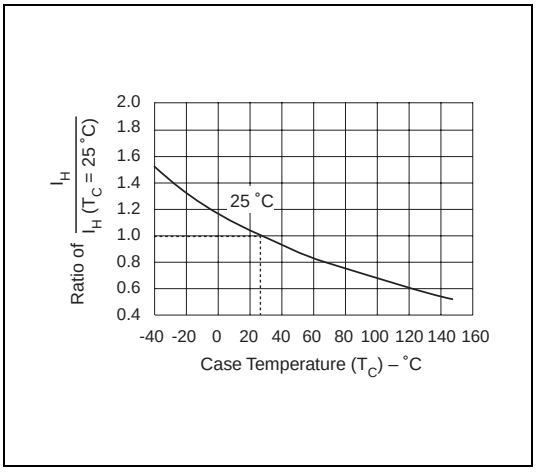
V-I Characteristics



t_r x t_d Pulse Wave-form



Normalized V_S Change versus Junction Temperature



Normalized DC Holding Current versus Case Temperature